

< C band internally matched power GaAs FET >

MGFC36V5258

5.2 – 5.8 GHz BAND / 4W

DESCRIPTION

The MGFC36V5258 is an internally impedance-matched GaAs power FET especially designed for use in 5.2 – 5.8 GHz band amplifiers. The hermetically sealed metal-ceramic package guarantees high reliability.

FEATURES

Internally matched to 50(ohm) system

- High output power
P1dB=4W (TYP.) @f=5.2 – 5.8GHz
- High power gain
GLP=10.0dB (TYP.) @f=5.2 – 5.8GHz
- High power added efficiency
P.A.E.=32% (TYP.) @f=5.2 – 5.8GHz

APPLICATION

- 5.2 – 5.8 GHz band microwave high power amplifier

QUALITY

- IG

RECOMMENDED BIAS CONDITIONS

- VDS=10V • ID=1.2A • RG=100ohm Refer to Bias Procedure

Absolute maximum ratings (Ta=25°C)

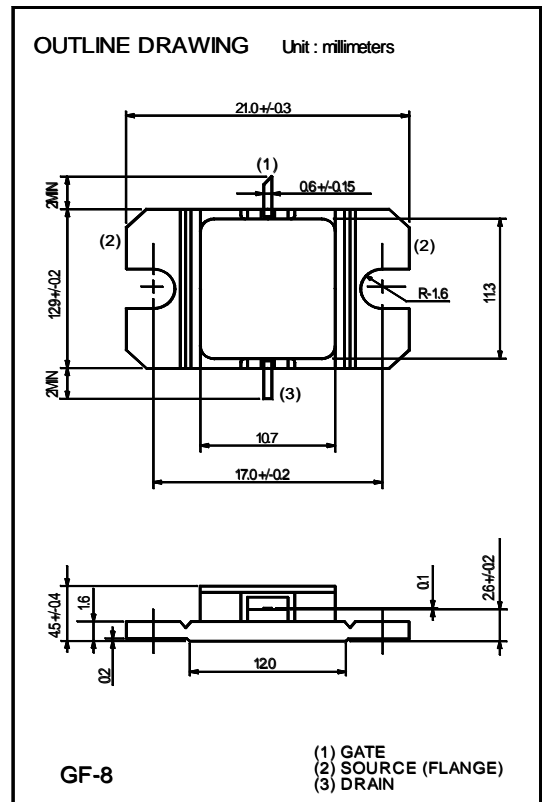
Symbol	Parameter	Ratings	Unit
VGDO	Gate to drain breakdown voltage	-15	V
VGSO	Gate to source breakdown voltage	-15	V
ID	Drain current	2.8	A
IGR	Reverse gate current	-10	mA
IGF	Forward gate current	21	mA
PT *1	Total power dissipation	25	W
Tch	Channel temperature	175	°C
Tstg	Storage temperature	-65 to +175	°C

*1 : Tc=25°C

Electrical characteristics (Ta=25°C)

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
IDSS	Saturated drain current	VDS=3V, VGS=0V	-	2.0	2.8	A
gm	Trans conductance	VDS=3V, ID=1.1A	-	2	-	S
VGS(off)	Gate to source cut-off voltage	VDS=3V, ID=10mA	-2	-3	-4	V
P1dB	Output power at 1dB gain compression	VDS=10V, ID(RF off)=1.2A	35	36	-	dBm
GLP *2	Linear Power Gain	f=5.2 – 5.8GHz	9	10	-	dB
P.A.E.	Power added efficiency	Pin=20dBm *2	-	32	-	%
ID	Drain current		-	1.1	1.4	A
Rth(ch-c) *3	Thermal resistance	delta Vf method	-	5	6	°C/W

*3 : Channel-case



Keep Safety first in your circuit designs!

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